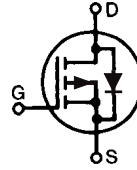


PolarP™ Power MOSFET

IXTR90P20P

P-Channel Enhancement Mode
Avalanche Rated

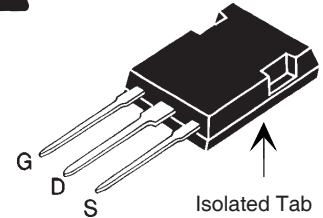


$$V_{DSS} = -200V$$

$$I_{D25} = -53A$$

$$R_{DS(on)} \leq 48m\Omega$$

ISOPLUS247 (IXTR)
E153432



G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	- 200	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	- 200	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	- 53	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	- 270	A
I_{AR}	$T_C = 25^\circ C$	- 90	A
E_{AS}	$T_C = 25^\circ C$	3.5	J
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	10	V/ns
P_D	$T_C = 25^\circ C$	312	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
T_{SOLD}	Plastic body for 10s	260	$^\circ C$
M_d	Mounting force	20..120/4.5..27	N/lb.
Weight		6	g

Features

- Silicon chip on Direct-Copper Bond (DCB) substrate
 - UL recognized package
 - Isolated mounting surface
 - 2500V electrical isolation
- Dynamic dv/dt rating
- Avalanche rated
- Fast intrinsic diode
- The rugged PolarP™ process
- Low Q_G
- Low Drain-to-Tab capacitance
- Low package inductance
 - easy to drive and to protect

Applications

- High side switching
- Push-pull amplifiers
- DC Choppers
- Automatic test equipment
- Load-Switch Application
- Fuel Injection Systems

Symbol	Test Conditions ($T_J = 25^\circ C$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = -250 \mu A$	- 200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 2.5		- 4.5 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 125^\circ C$			- 50 μA - 250 μA
$R_{DS(on)}$	$V_{GS} = -10V$, $I_D = -45A$, Note 1			48 m Ω

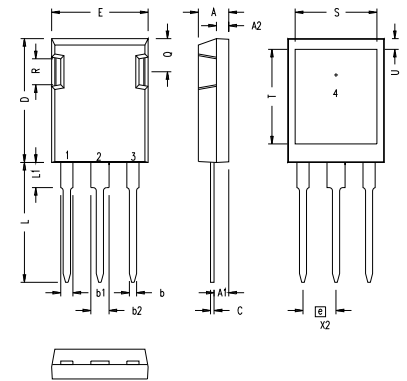
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = -10\text{V}$, $I_D = -45\text{A}$, Note 1	30	51	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = -25\text{V}$, $f = 1\text{MHz}$		12	nF
C_{oss}			2210	pF
C_{rss}			250	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = -45\text{A}$ $R_G = 1\Omega$ (External)		32	ns
t_r			60	ns
$t_{d(off)}$			89	ns
t_f			28	ns
$Q_{g(on)}$	$V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = -45\text{A}$		205	nC
Q_{gs}			45	nC
Q_{gd}			80	nC
R_{thJC}				0.40 $^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			- 90 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			- 360 A
V_{SD}	$I_F = -45\text{A}$, $V_{GS} = 0\text{V}$, Note 1			- 3.2 V
t_{rr}	$I_F = -45\text{A}$, $-di/dt = -150\text{A}/\mu\text{s}$ $V_R = -100\text{V}$, $V_{GS} = 0\text{V}$		315	ns
Q_{RM}			6.6	μC
I_{RM}			- 42	A

Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

ISOPLUS247 (IXTR) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - NO CONNECTION

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ 25°C

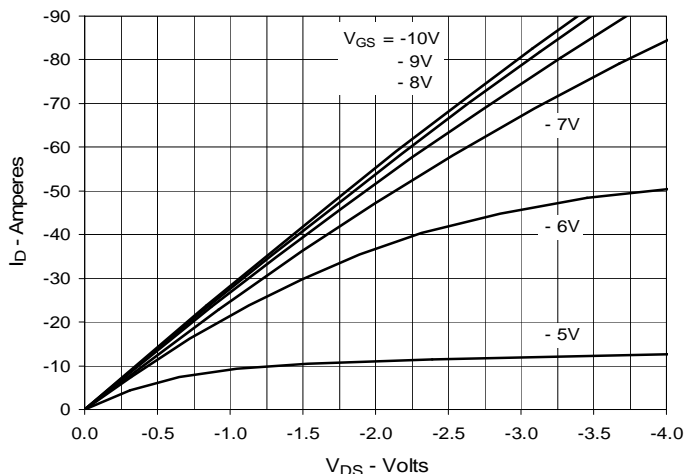


Fig. 2. Extended Output Characteristics @ 25°C

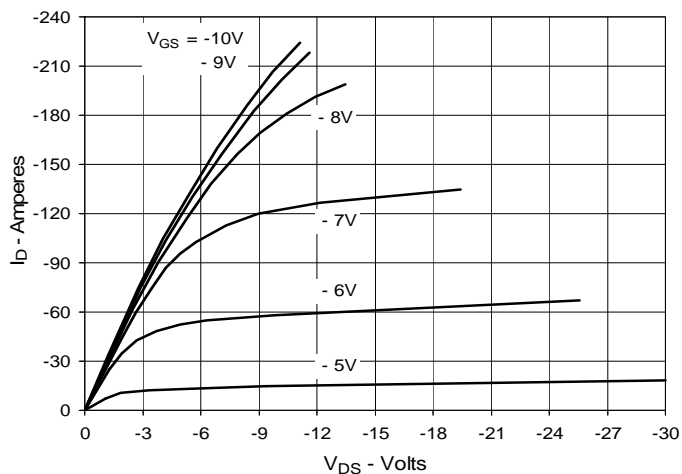


Fig. 3. Output Characteristics @ 125°C

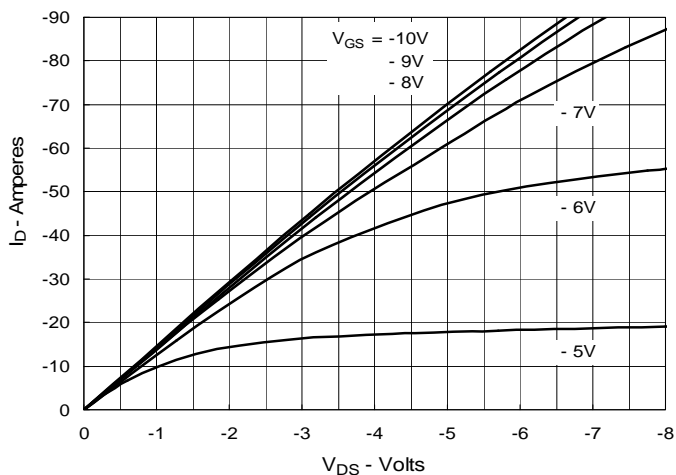


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = -45A$ vs. Junction Temperature

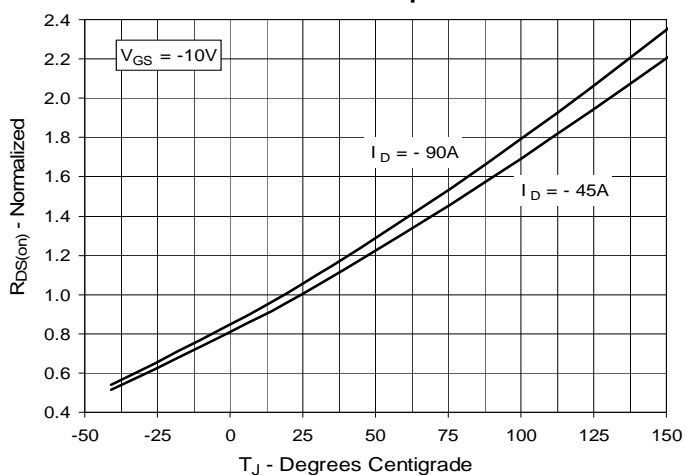


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = -45A$ vs. Drain Current

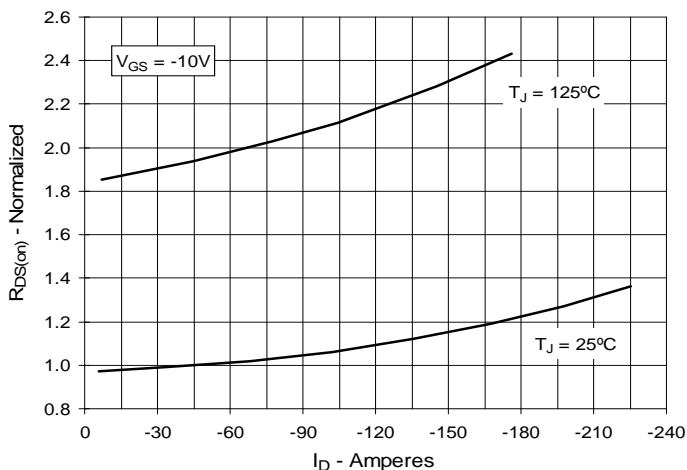


Fig. 6. Maximum Drain Current vs. Case Temperature

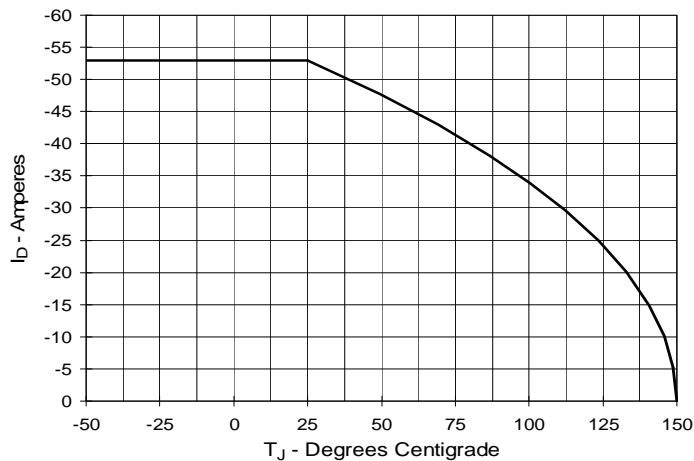


Fig. 7. Input Admittance

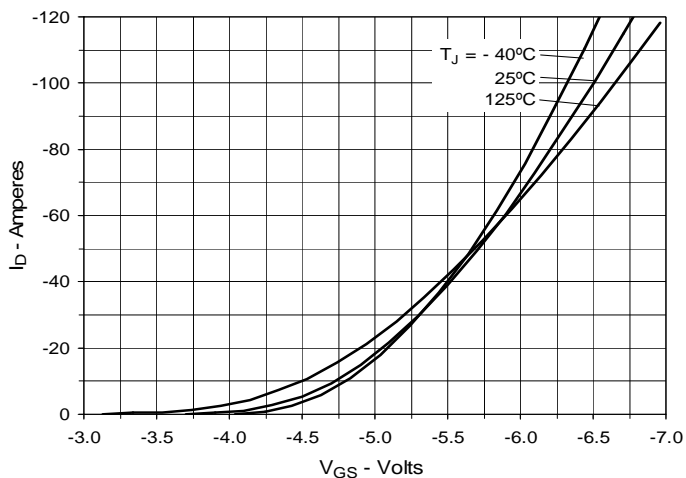


Fig. 8. Transconductance

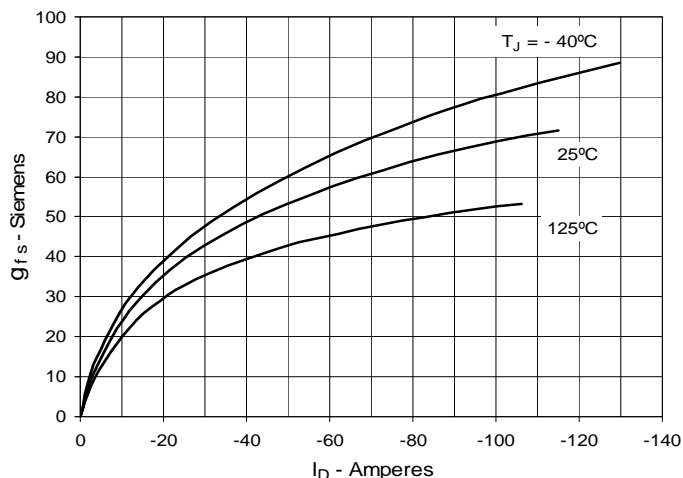


Fig. 9. Forward Voltage Drop of Intrinsic Diode

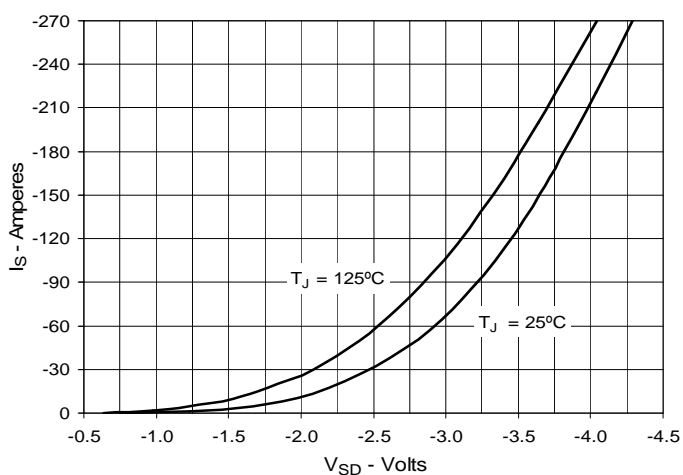


Fig. 10. Gate Charge

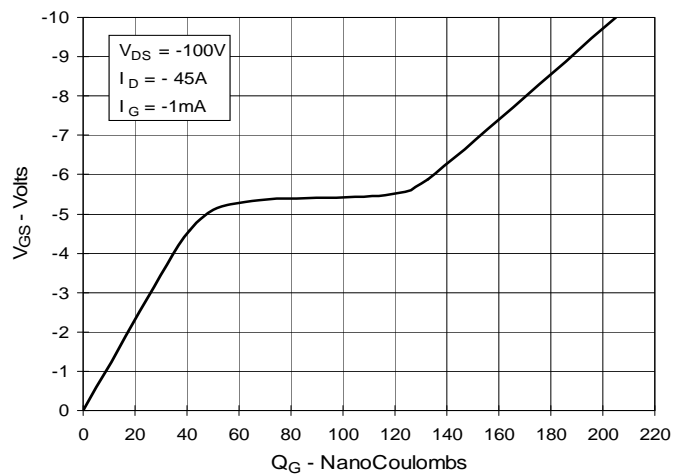


Fig. 11. Capacitance

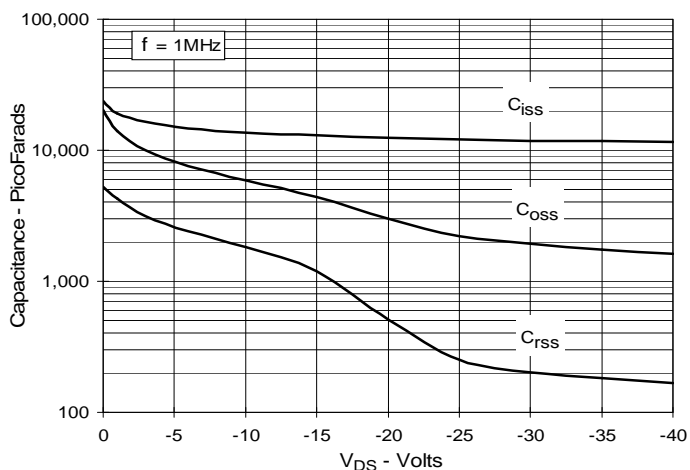


Fig. 12. Forward-Bias Safe Operating Area

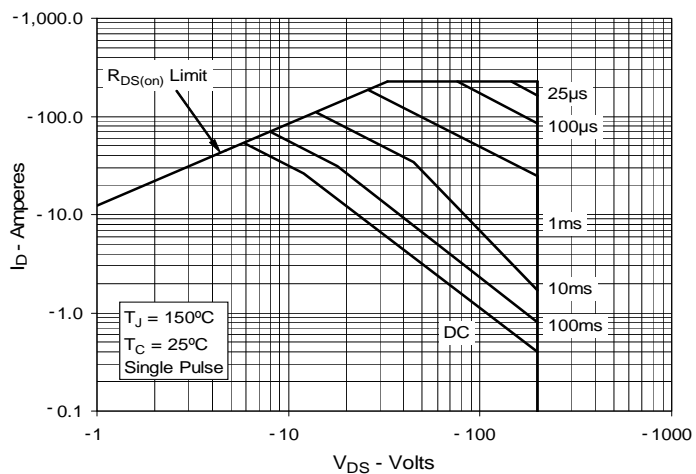


Fig. 13. Maximum Transient Thermal Impedance

